

### **INCHANGE SEMICONDUCTOR**

# isc N-Channel MOSFET Transistor

### **IXTA160N10T**

1.28

0.2

0.39

2.82

| RDS(<br>• Fully ch<br>• 100% a<br>• Minimu<br>perform<br>• APPLIA<br>• DC/DC | drain-source on-resistance:<br>on) $\leq$ 7.0m $\Omega$ @V <sub>GS</sub> =10V<br>haracterized avalanche voltage and<br>avalanche tested<br>im Lot-to-Lot variations for robust d<br>nance and reliable operation |              |      | 1 2 3<br>D2PA | ĸ           |                       |                       |             |
|--|--|--------------|------|---------------|-------------|-----------------------|-----------------------|-------------|
| -  | LUTE MAXIMUM RATINGS(Ta=25   | °C)<br>VALUE | UNIT |               | A<br>B      | K                     | -                     | L<br>S<br>S |
| V <sub>DSS</sub>   | Drain-Source Voltage   | 100          | V    | c             | D           |                       | Q                     | U           |
| V <sub>GS</sub>  | Gate-Source Voltage  | ±30          | V    | - Jue         | H           | ſ                     | R                     | y.          |
| ID   | Drain Current-Continuous   | 160          | А    | - F++-        | ⊢∔G         |                       |                       | V           |
| I <sub>DM</sub>  | Drain Current-Single Pulsed  | 430          | А    | -             | DIM         | MIN<br>10             | MAX                   |             |
| PD   | Total Dissipation @Tc=25°C   | 430          | W    |               | A<br>B<br>C | 6.6                   | 6.8<br>15.25          |             |
| Tj   | Operating Junction Temperature   | -55~175      | °C   |               | D<br>F<br>G | 10.15<br>0.76<br>1.26 | 10.17<br>0.78<br>1.28 |             |
|  | Storage Temperature  | -55~175      | °C   | -             | Н           | 1.4                   | 1.6                   |             |
| T <sub>stg</sub>   |  |              |      |               | J           | 1.33<br>0.4           | 1.35<br>0.6           |             |

| SYMBOL PARAMETER     |                                     | MAX  | UNIT |  |  |  |
|----------------------|-------------------------------------|------|------|--|--|--|
| R <sub>th(j-c)</sub> | Junction-to-case thermal resistance | 0.35 | °C/W |  |  |  |

s

U

V

1.26 0.0

0.37

W 2.80



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#### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL              | PARAMETER  | CONDITIONS   | MIN | МАХ  | UNIT |
|---------------------|--|--|-----|------|------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage   | V <sub>GS</sub> = 0V; ID = 250 μ A   | 100 |      | V    |
| $V_{GS(th)}$        | Gate Threshold Voltage   | V <sub>DS</sub> = V <sub>GS</sub> ; ID = 250 μ A                                 | 2.5 | 4.5  | V    |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance $V_{GS}$ =10V; I <sub>D</sub> = 25A         |  |     | 7.0  | mΩ   |
| I <sub>GSS</sub>    | Gate-Source Leakage Current V <sub>GS</sub> = ±20V;V <sub>DS</sub> =0V |  |     | ±200 | nA   |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V                        |     | 5    |      |
|                     |  | V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V;T <sub>J</sub> = 150°C |     | 250  | μA   |
| Vsd                 | Diode forward voltage  | I <sub>F</sub> = 25A; V <sub>GS</sub> = 0V                                       |     | 1.0  | V    |

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